

# NGTB40N65IHRWG

## IGBT with Monolithic Reverse Conducting Diode

This Insulated Gate Bipolar Transistor (IGBT) features robust and cost effective Field Stop (FS2) trench construction with a monolithic RC Diode. It provides a cost effective Solution for applications where diode losses are minimal. The IGBT is optimized for low conduction losses (low  $V_{CEsat}$ ) and is well suited for resonant or soft switching applications.

### Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Conduction Design for Soft Switching Application
- Reduced Power Dissipation in Inducting Heating Application
- Reliable and Cost Effective Single Die Solution
- This is a Pb-Free Device

### Typical Applications

- Inductive Heating
- Air Conditioning PFC
- Welding

### ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	$V_{CES}$	650	V
Collector current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_C$	80 40	A
Pulsed collector current, $t_{pulse}$ limited by $T_{Jmax}$ , 10 $\mu\text{s}$ pulse, $V_{GE} = 15\text{ V}$	$I_{CM}$	160	A
Diode forward current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_F$	80 40	A
Diode pulsed current, $t_{pulse}$ limited by $T_{Jmax}$ , 10 $\mu\text{s}$ pulse, $V_{GE} = 0\text{ V}$	$I_{FM}$	160	A
Gate-emitter voltage Transient Gate-emitter voltage ( $t_{pulse} = 5\text{ }\mu\text{s}$ , $D < 0.10$ )	$V_{GE}$	$\pm 20$ $\pm 25$	V
Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$P_D$	405 202	W
Operating junction temperature range	$T_J$	$-40$ to $+175$	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	$-55$ to $+175$	$^\circ\text{C}$
Lead temperature for soldering, 1/8" from case for 5 seconds	$T_{SLD}$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



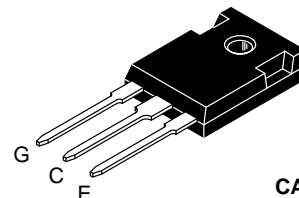
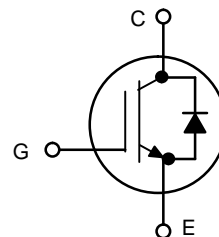
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40 A, 650 V

$V_{CEsat} = 1.55\text{ V}$

$E_{off} = 0.42\text{ mJ}$



TO-247  
CASE 340AL

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
NGTB40N65IHRWG	TO-247 (Pb-Free)	30 Units / Rail

# NGTB40N65IHRWG

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case	$R_{\theta JC}$	0.37	$^{\circ}\text{C/W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\text{ }\mu\text{A}$	$V_{(BR)CES}$	650	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^{\circ}\text{C}$	$V_{CEsat}$	– –	1.55 1.95	1.7 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 350\text{ }\mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 175^{\circ}\text{C}$	$I_{CES}$	– –	– 1.0	0.3 –	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	–	–	100	nA

### DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$	–	4628	–	pF
Output capacitance		$C_{oes}$	–	148	–	
Reverse transfer capacitance		$C_{res}$	–	126	–	
Gate charge total	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	$Q_g$	–	190	–	nC
Gate to emitter charge		$Q_{ge}$	–	38	–	
Gate to collector charge		$Q_{gc}$	–	90	–	

### SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-off delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 40\text{ A}$ $R_g = 10\text{ }\Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(off)}$	–	197	–	ns
Fall time		$t_f$	–	74	–	
Turn-off switching loss		$E_{off}$	–	0.42	–	mJ
Turn-off delay time	$T_J = 175^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 40\text{ A}$ $R_g = 10\text{ }\Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(off)}$	–	210	–	ns
Fall time		$t_f$	–	106	–	
Turn-off switching loss		$E_{off}$	–	0.7	–	mJ

### DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 40\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 40\text{ A}, T_J = 175^{\circ}\text{C}$	$V_F$	– –	1.50 1.70	1.80 –	V
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NGTB40N65IHRWG

## TYPICAL CHARACTERISTICS

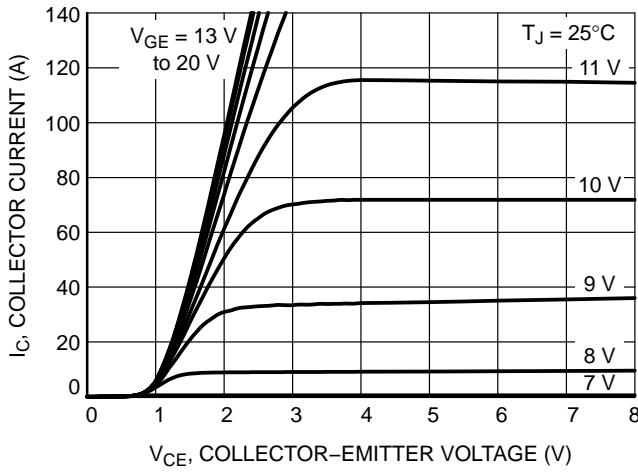


Figure 1. Output Characteristics

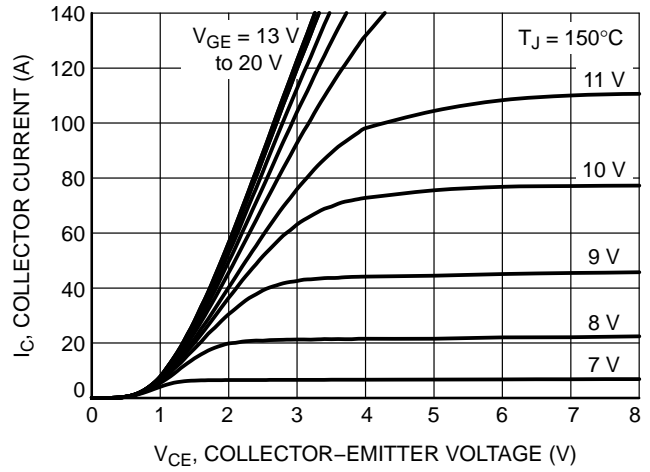


Figure 2. Output Characteristics

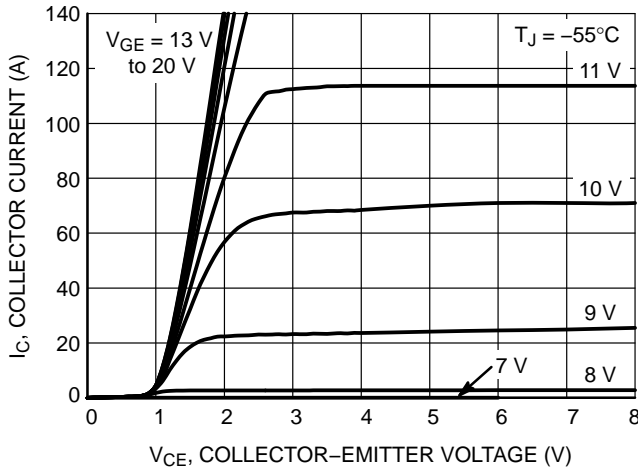


Figure 3. Output Characteristics

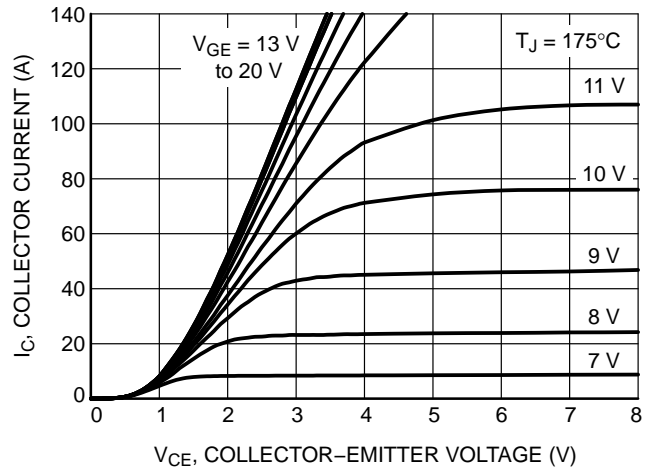


Figure 4. Output Characteristics

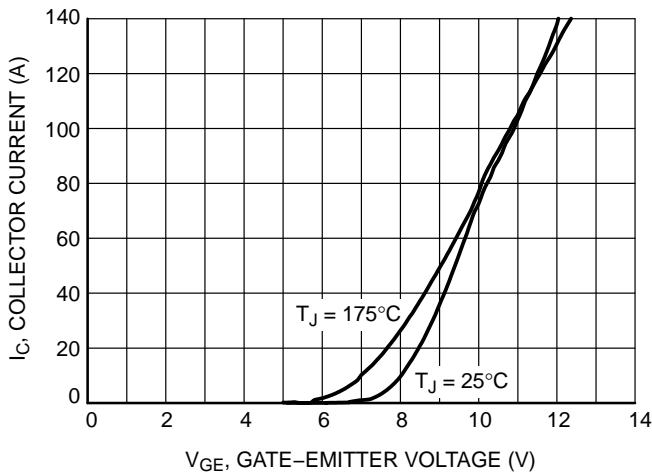


Figure 5. Typical Transfer Characteristics

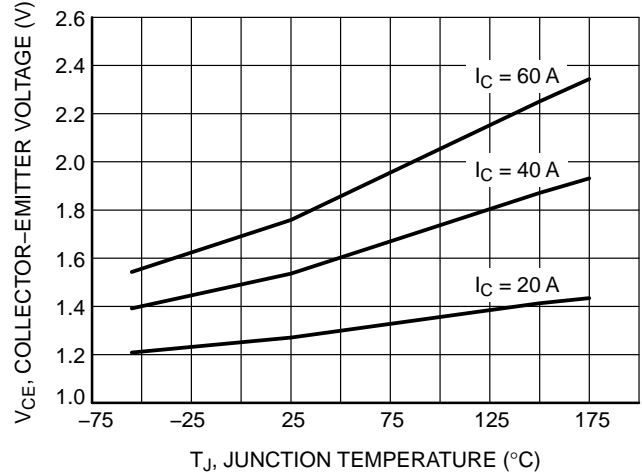


Figure 6.  $V_{CE(sat)}$  vs.  $T_J$

# NGTB40N65IHRWG

## TYPICAL CHARACTERISTICS

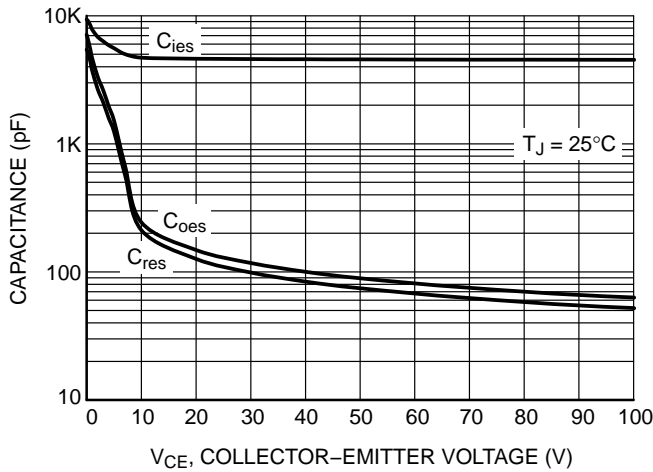


Figure 7. Typical Capacitance

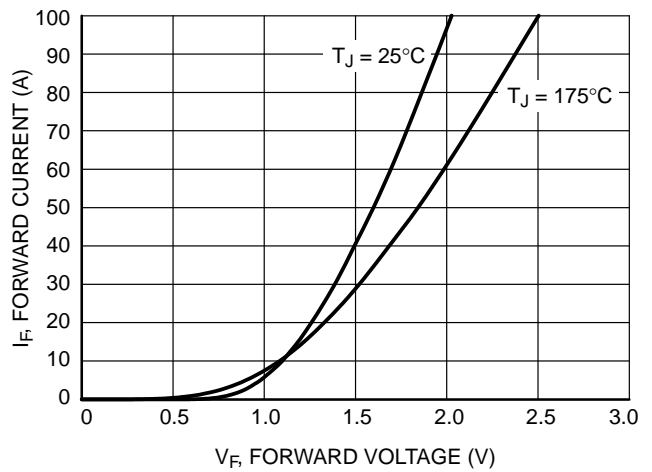


Figure 8. Diode Forward Characteristics

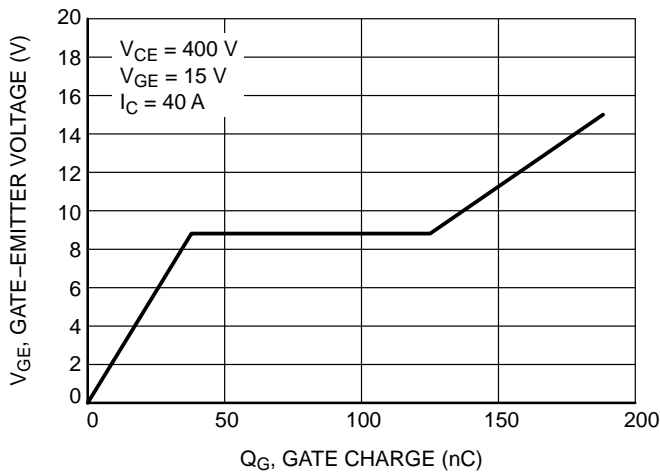


Figure 9. Typical Gate Charge

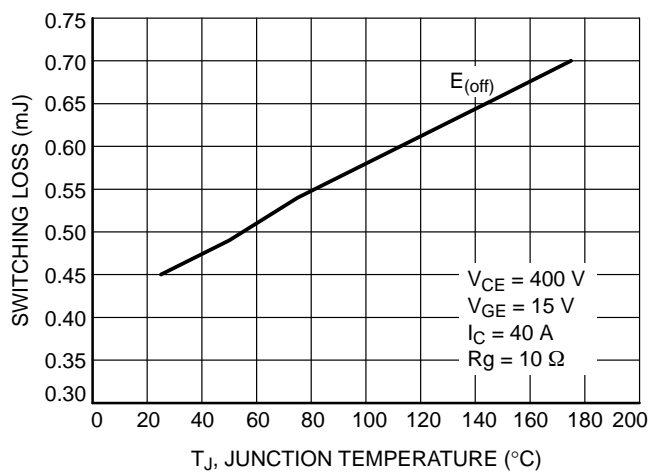


Figure 10. Switching Loss vs. Temperature

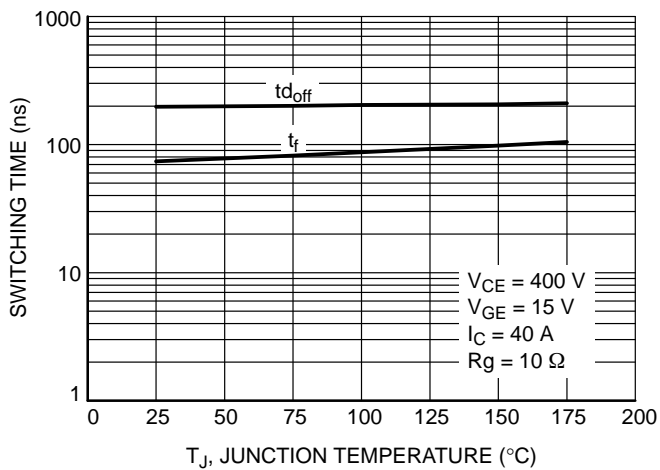


Figure 11. Switching Time vs. Temperature

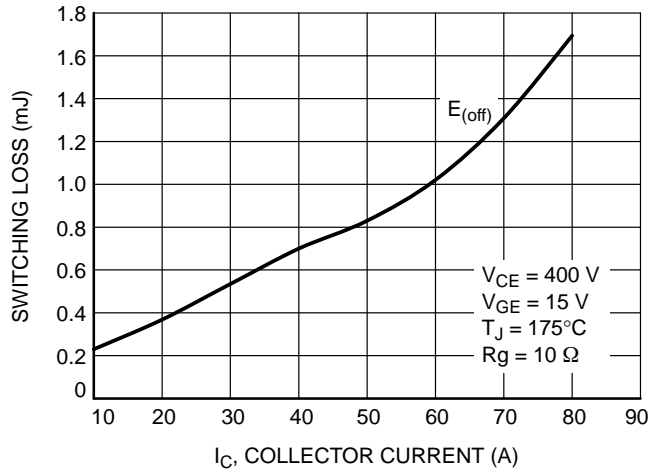


Figure 12. Switching Loss vs.  $I_C$

# NGTB40N65IHRWG

## TYPICAL CHARACTERISTICS

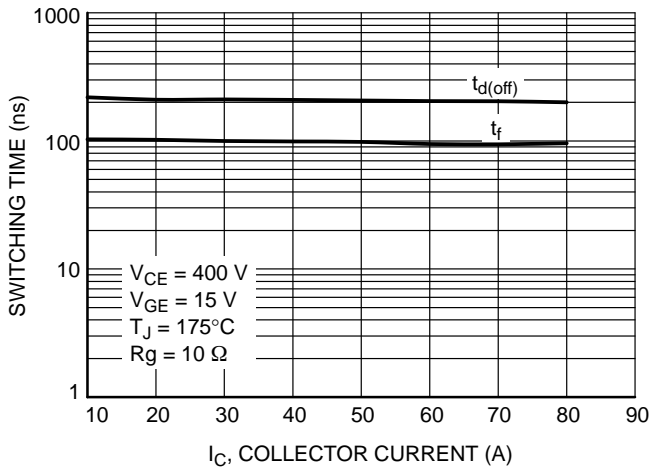


Figure 13. Switching Time vs.  $I_C$

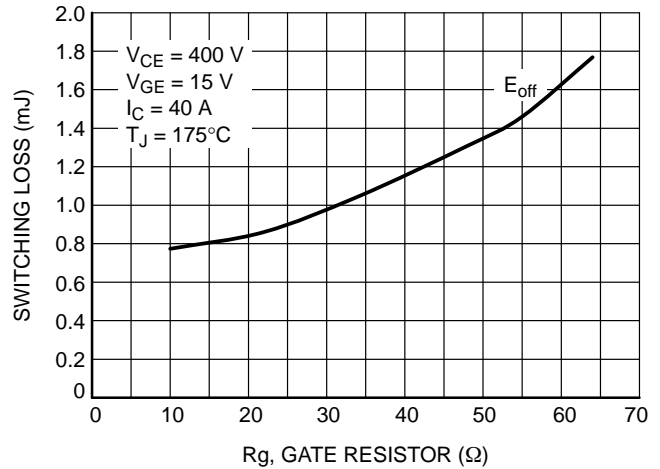


Figure 14. Switching Loss vs.  $R_g$

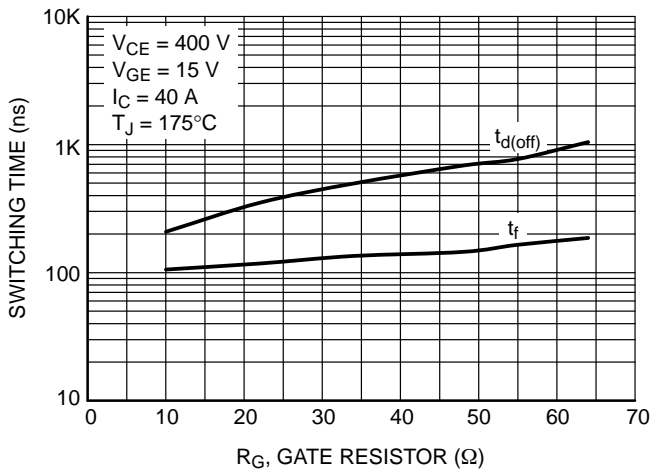


Figure 15. Switching Time vs.  $R_g$

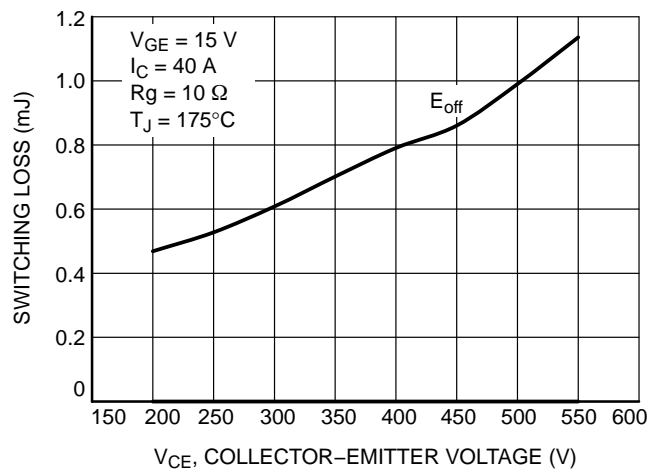


Figure 16. Switching Loss vs.  $V_{CE}$

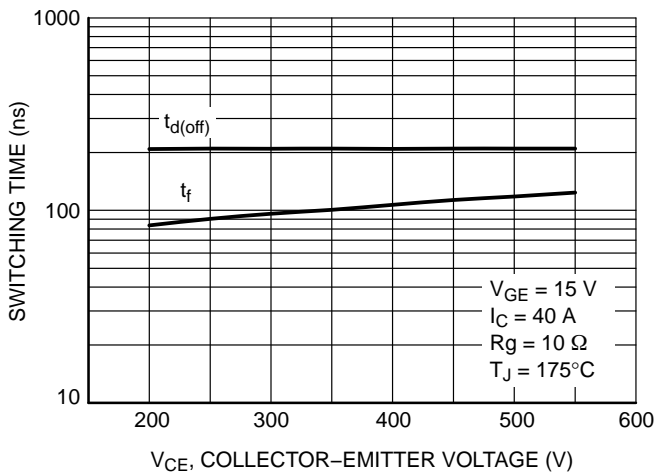


Figure 17. Switching Time vs.  $V_{CE}$

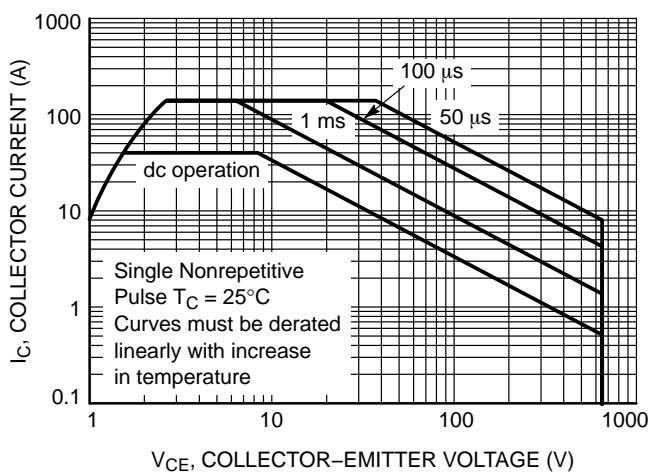


Figure 18. Safe Operating Area

# NGTB40N65IHRWG

## TYPICAL CHARACTERISTICS

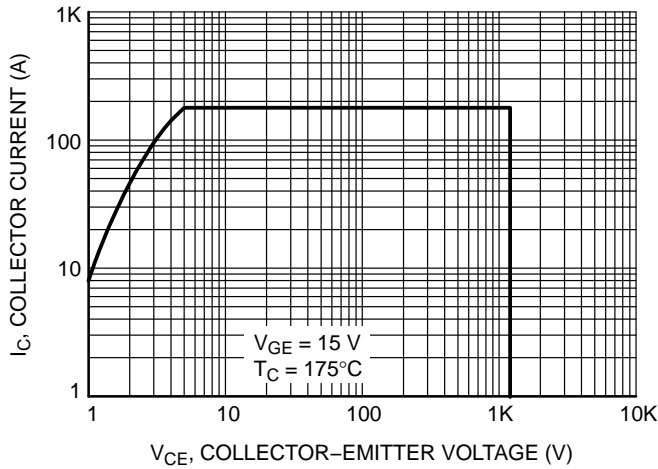


Figure 19. Reverse Bias Safe Operating Area

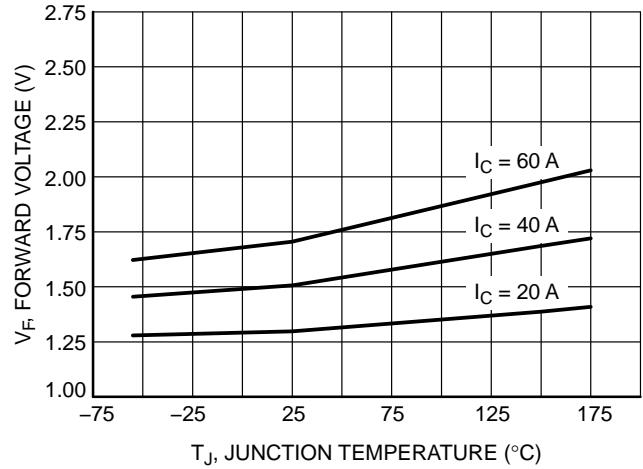


Figure 20. Forward Voltage vs. Junction Temperature

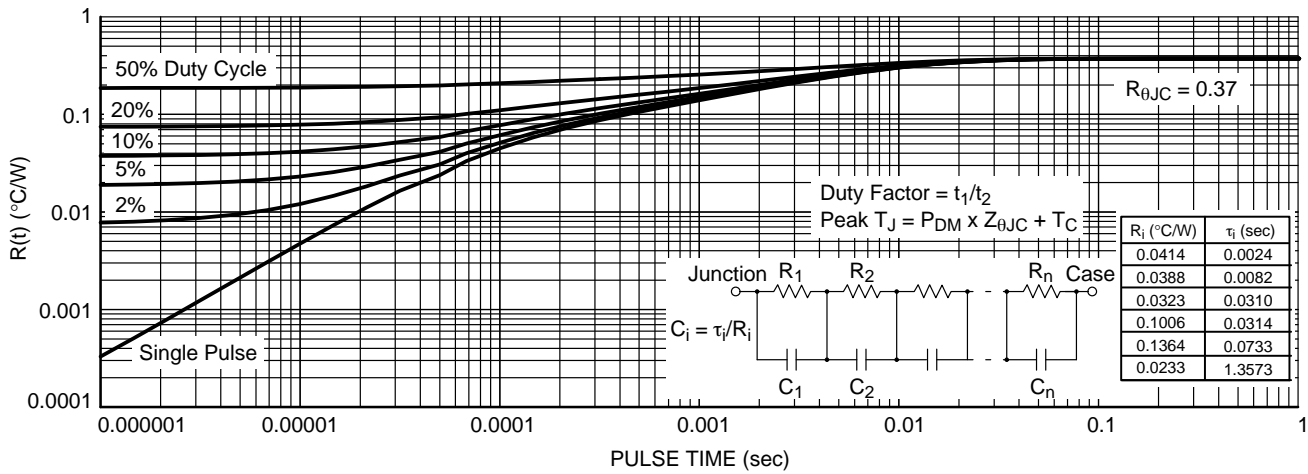


Figure 21. IGBT Transient Thermal Impedance

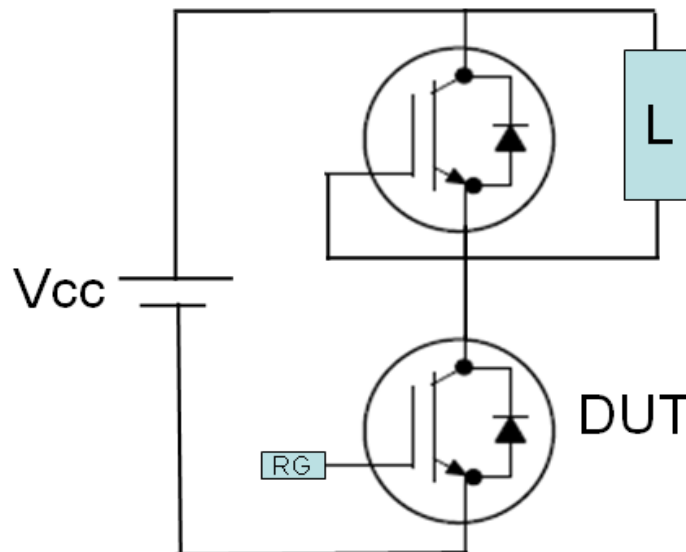


Figure 22. Test Circuit for Switching Characteristics

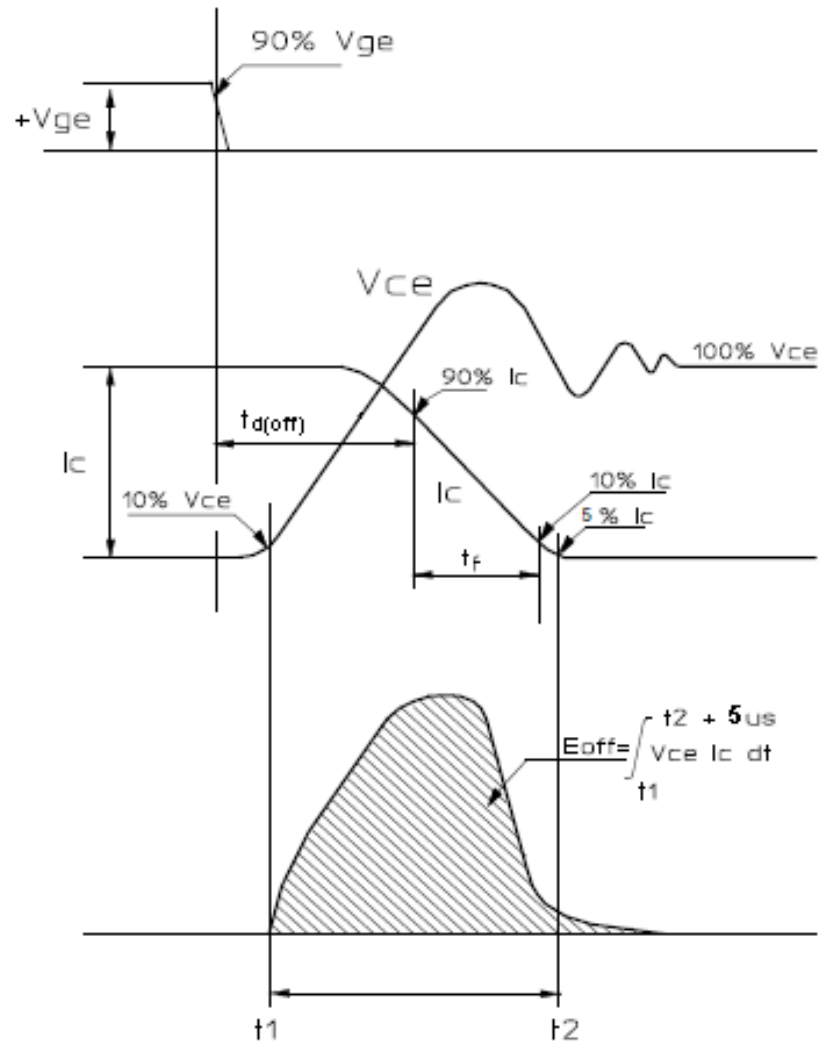


Figure 23. Definition of Turn Off Waveform

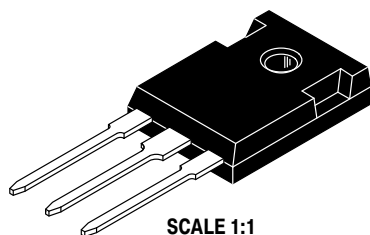
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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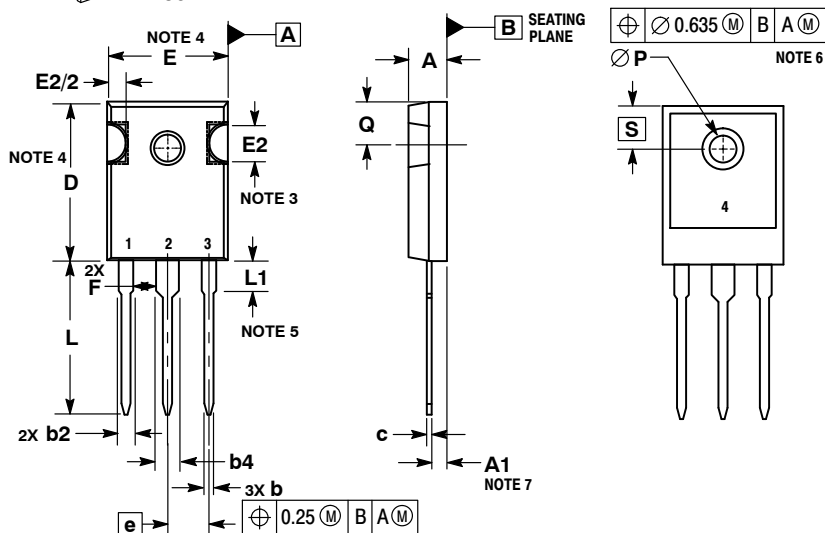


## TO-247 CASE 340AL ISSUE D

DATE 17 MAR 2017



SCALE 1:1

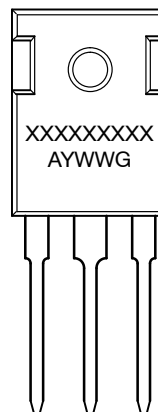


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. ØP SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS	
	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

### GENERIC MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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